



20V NPN HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEX} > 70V
- BV_{CEO} > 20V
- BV_{ECO} > 4.5V
- I_C = 9A High Continuous Current
- Low Saturation Voltage V_{CE(sat)} < 35mV @ 1A
- $R_{CE(sat)} = 20m\Omega$
- Complementary PNP Type: ZXTP19020DG
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

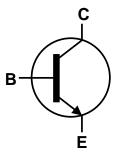
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

Applications

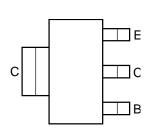
- PSU Start-Up Circuit
- DC-DC Converters
- Motor Drive
- Relay, Lamp and Solenoid Drive







Device Symbol



Top View Pin-Out

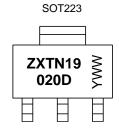
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN19020DGTA	AEC-Q101	ZXTN19020D	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTN19020D = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or \overline{W} W = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	70	V
Collector-Emitter Voltage (forward blocking)	V _{CEX}	70	V
Collector-Emitter Voltage	V _{CEO}	20	V
Emitter-Collector Voltage (reverse blocking)	V _{ECX}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	9	Α
Base Current	I _B	1	Α
Peak Pulse Current	Ісм	20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1.2 9.6		
Power Dissipation	(Note 6)	D	1.6 12.8	W mW/°C	
Linear Derating Factor	(Note 7)	P _D	3 24		
	(Note 8)		5.3 42		
	(Note 5)		104		
Thermal Desistance, Junction to Ambient	(Note 6)		78		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	42	°C/W	
	(Note 8)		23.5		
Thermal Resistance, Junction to Lead (Note 9)		$R_{\theta JL}$	16		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

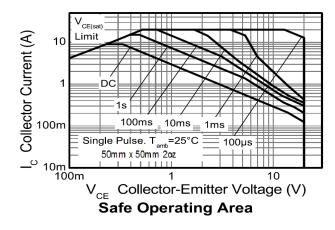
Notes: 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

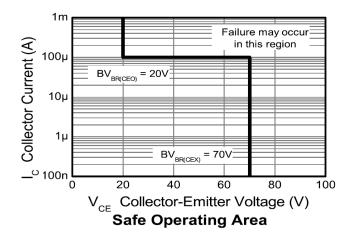
6. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.

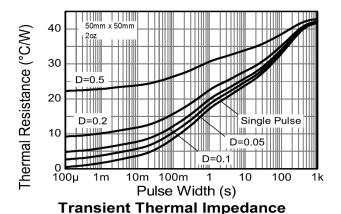
- 7. Same as Note 6, except the device is mounted on 50mm x 50mm 2oz copper.
- 8. Same as Note 8 measured at t<5 seconds.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

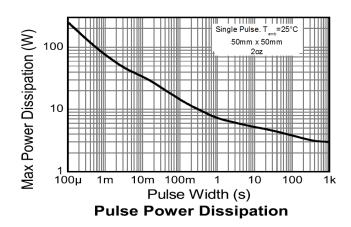


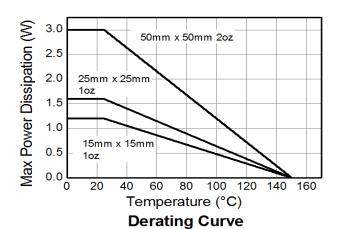
Thermal Characteristics and Derating Information (@T_A = +25°C, unless otherwise specified.)













Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

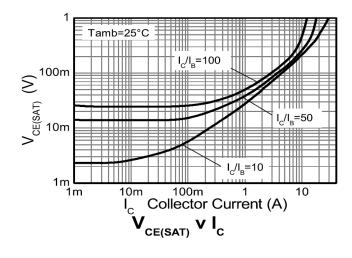
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	70	100	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (forward blocking)	BV _{CEX}	70	100		٧	$I_C = 100\mu A$, $R_{BE} < 1k\Omega$ or $-1V < V_{BE} > 0.25V$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	20	30	-	V	$I_C = 10mA$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	6	8.4	_	V	$I_C = 100\mu A, R_{BC} < 1k\Omega or$ 0.25V < $V_{BC} > -0.25V$
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECO}	4.5	5.7	_	V	I _E = 100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.4	-	V	$I_E = 100\mu A$
Collector Cut-Off Current	1	-	< 1	50	nA	V _{CB} = 70V
Collector Cut-Oil Current	Ісво	-	-	0.5	μΑ	$V_{CB} = 70V, T_A = +100^{\circ}C$
Collector-Emitter Cut-Off Current	I _{CEX}	_	_	100	nA	$V_{CE} = 70V, R_{BE} < 1k\Omega \text{ or}$ -1V < $V_{BE} > 0.25V$
Emitter Cut-Off Current	I _{EBO}	_	< 1	50	nA	$V_{EB} = 5.6V$
		_	27	35	mV	$I_C = 1A$, $I_B = 100mA$
	VCE(sat)	_	50	70	mV	$I_C = 1A$, $I_B = 10mA$
Collector-Emitter Saturation Voltage (Note 11)		-	80	100	mV	$I_C = 2A$, $I_B = 20mA$
Collector-Emitter Saturation Voltage (Note 11)		_	63	80	mV	$I_C = 2A$, $I_B = 40mA$
		=	85	110	mV	$I_C = 4A$, $I_B = 400mA$
		_	200	250	mV	$I_C = 9A$, $I_B = 450mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	1040	1150	mV	$I_C = 9A$, $I_B = 450mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	=	910	1050	mV	$I_C = 9A$, $V_{CE} = 2V$
		300	450	900	-	$I_C = 100 \text{mA}, V_{CE} = 2 \text{V}$
		260	390	-	_	$I_C = 2A$, $V_{CE} = 2V$
DC Current Gain (Note 11)	h _{FE}	130	175	-	-	$I_C = 9A$, $V_{CE} = 2V$
		50	75	-	-	$I_C = 15A, V_{CE} = 2V$
		=	30	=	=	$I_C = 20A, V_{CE} = 2V$
Current Gain-Bandwidth Product (Note 11)	f⊤	-	160	-	MHz	$V_{CE} = 10V, I_{C} = 50mA,$ f = 100MHz
Input Capacitance (Note 11)	C_{ibo}	-	297	400	pF	$V_{EB} = 0.5V$, $f = 1MHz$
Output Capacitance (Note 11)	C_obo	=	32.6	40	pF	$V_{CB} = 10V$, $f = 1MHz$
Delay Time	t _d	-	129	-	ns	
Rise Time	t _r	_	96	-	ns	$I_C = 1A$, $V_{CC} = 10V$,
Storage Time	t _s	=	398	-	ns	$I_{B1} = -I_{B2} = 10mA$
Fall Time	t _f	_	90	_	ns	

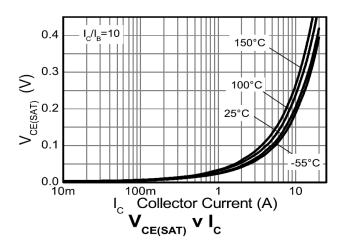
Note:

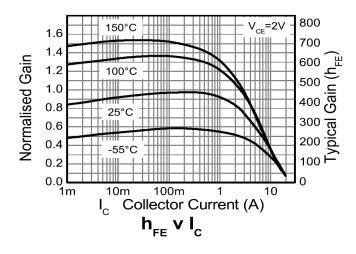
11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

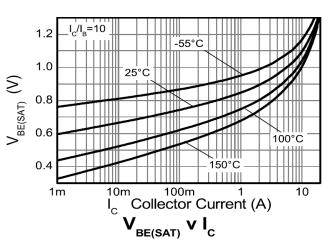


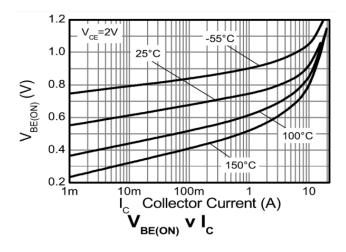
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







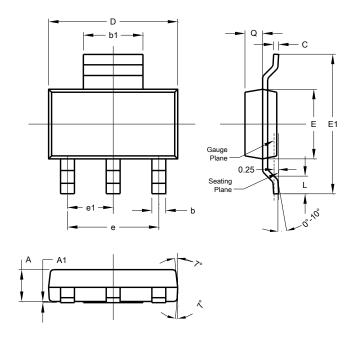






Package Outline Dimensions

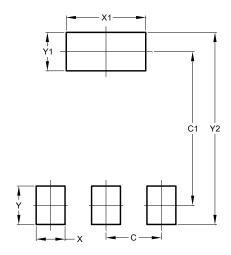
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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